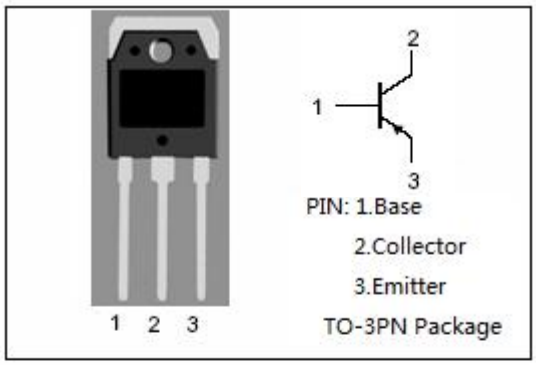
SPTECH Silicon PNP Power Transistor



DESCRIPTION

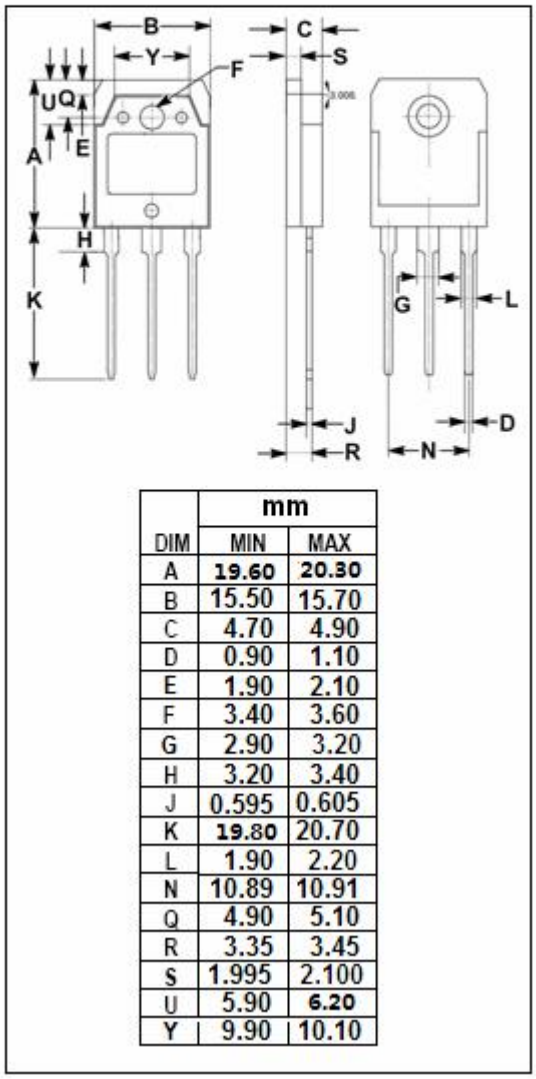
- Collector-Emitter Breakdown Voltage-
  $V_{(BR)CEO}$= -140V(Min)
- Good Linearity of h_{FE}
- High Power Dissipation
- Complement to Type 2SC2581

APPLICATIONS

- Designed for audio and general purpose applications.

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-140	V
V_{CEO}	Collector-Emitter Voltage	-140	V
V_{EBO}	Emitter-Base Voltage	-6	V
I_C	Collector Current-Continuous	-10	A
I_B	Base Current-Continuous	-4	A
P_C	Collector Power Dissipation @ T_C=25℃	100	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃



DIM	mm MIN	MAX
A	19.60	20.30
B	15.50	15.70
C	4.70	4.90
D	0.90	1.10
E	1.90	2.10
F	3.40	3.60
G	2.90	3.20
H	3.20	3.40
J	0.595	0.605
K	19.80	20.70
L	1.90	2.20
N	10.89	10.91
Q	4.90	5.10
R	3.35	3.45
S	1.995	2.100
U	5.90	6.20
Y	9.90	10.10

SPTECH Silicon PNP Power Transistor

ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= -50mA; I_B= 0	-140			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= -5A; I_B= -0.5A			-2.0	V
I_{CBO}	Collector Cutoff Current	V_{CB}= -140V; I_E= 0			-100	μA
I_{EBO}	Emitter Cutoff Current	V_{EB}= -6V; I_C= 0			-100	μA
h_{FE}	DC Current Gain	I_C= -3A; V_{CE}= -4V	30			
f_T	Current-Gain—Bandwidth Product	I_E= 0.5A; V_{CE}= -12V		20		MHz

Switching Times

t_r	Rise Time	I_C= -5A, R_L= 12Ω, I_{B1}= -I_{B2}= -0.5A, V_{CC}= -60V		0.3		μs
t_{stg}	Storage Time			0.9		μs
t_f	Fall Time			0.2		μs